CLAIMS

1. An epoxy resin composition for encapsulating semiconductors comprising (A) an epoxy resin, (B) a phenol resin, (C) an inorganic filler, (D) a curing accelerator, (E) a glycerol tri-fatty acid ester produced by dehydration condensation reaction of glycerol and a saturated fatty acid with a carbon atom content of 24-36, and (F) a hydrotalcite compound.

2. The epoxy resin composition for encapsulating semiconductors according to claim 1, wherein the hydrotalcite compound is a compound shown by the following formula (1) and/or its sintered material,

$$Mg_xAl_y(OH)_zCO_3 \cdot nH_2O \qquad (1)$$

wherein x, y, z, and n are positive numbers.

3. The epoxy resin composition for encapsulating semiconductors according to claim 2, wherein the hydrotalcite compound is a hydrotalcite of the above formula (1) in which $0.15 \leq (y/x+y) \leq 0.35$, $1.8 \leq (z/x+y) \leq 2.5$, and $0 \leq n \leq 5$ and/or its sintered material.

4. The epoxy resin composition for encapsulating semiconductors according to claim 1, wherein the hydrotalcite compound is a compound shown by the formula $Mg_6Al_2(OH)_{16}CO_3 \cdot 4H_2O$.

5. A semiconductor device comprising a semiconductor element encapsulated using the epoxy resin composition according to any one of claims 1-4.